

High-Temperature Silicon Carbide (SiC) Half-Bridge Power Module

N-Channel MOSFET Version

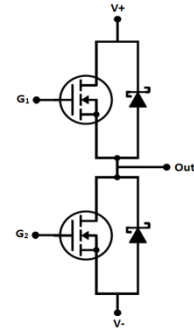
FEATURES

- High temperature: $T_{c(max)} = 225\text{ }^{\circ}\text{C}$
 $T_{J(max)} = 225\text{ }^{\circ}\text{C}$
- AS9100:Rev. C-certified manufacturing, traceable throughout value chain
- Ultra-fast switching (<30 ns), low inductance
- Enables high system efficiency
- Low profile, small form factor

1200 V / 225 A / 13.5 mΩ

APPLICATIONS

- High-efficiency converters / inverters
- Motor drives
- Aerospace: Military & Commercial
- Smart grid/grid-tie distributed generation
- Industrial and automotive traction drives



DESCRIPTION

The APE HT-2201 Silicon Carbide (SiC) half-bridge power module was designed specifically to address the growing demand for higher power densities, higher temperatures, and higher switching frequencies.

COMPANION PARTS

Maximum performance may be obtained through use of the companion high-temperature gate driver, part number APE MTGD2-2011, designed especially for driving the Silicon Carbide module.

Power Module Absolute Maximum Ratings ($T_c = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Condition(s)	Value	Units
V_{DSS}	Drain-source voltage		1200	V
V_{GSS}	Gate-source voltage		-5 to 20	V
I_D	Continuous drain current	$T_c = 25\text{ }^{\circ}\text{C}$	225	A
		$T_c = 100\text{ }^{\circ}\text{C}$	175	
		$T_c = 200\text{ }^{\circ}\text{C}$	80	
I_{DM}	Peak pulsed drain current	Pulse width $\leq 10\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	TBD	A
P_D	Maximum power dissipated		1600	W
$T_{C(max)}$	Maximum case temperature ¹		225	$^{\circ}\text{C}$
$T_{J(min)}$	Minimum operating junction temperature		- 50	$^{\circ}\text{C}$
$T_{J(max)}$	Maximum operating junction temperature		225	
T_{stg}	Storage temperature		- 50 to 225	$^{\circ}\text{C}$
V_{isol}	Insulation test voltage	AC, 1 min.	TBD	V
		AC, 1 s.	TBD	

¹The packaging materials have been qualified at this temperature.

Switch Position Electrical Characteristics ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Symbols	Parameter	Condition(s)	Values			Units
			Min.	Typical	Max.	
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	1200	-	-	V
$V_{GS(th)}$	Gate-source threshold voltage	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	-	2.1	-	V
		$V_{DS} = V_{GS}, I_D = 1\text{ mA}, T_J = 205\text{ }^\circ\text{C}$	-	1.1	-	
I_{DSS}	Drain-source leakage current	$V_{GS} = -5\text{ V}, V_{DS} = 1200\text{ V}$	-	-	200	μA
		$V_{GS} = -5\text{ V}, V_{DS} = 1200\text{ V}, T_J = 205\text{ }^\circ\text{C}$	-	-	2000	
I_{GSS}	Gate-source leakage current	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	-	-	250	nA
$R_{DS(on)}$	Drain-source turn-on resistance	$V_{GS} = 20\text{ V}, I_D = 75\text{ A}$	-	13.5	-	m Ω
		$V_{GS} = 20\text{ V}, I_D = 75\text{ A}, T_J = 225\text{ }^\circ\text{C}$	-	26.6	-	
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}$	-	11,490	-	pF
C_{oss}	Output capacitance	$V_{DS} = 800\text{ V}$	-	720	-	
C_{rss}	Reverse transfer capacitance	$f = 1\text{ MHz}$	-	78	-	
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 600\text{ V}, V_{GS} = -4\text{ to }20\text{ V}$ $I_D = 120\text{ A}$ $R_{G(ext)} = 0\text{ }\Omega, R_L = 60\text{ }\Omega$	-	36	-	ns
t_{rv}	Rise time		-	20	-	
$t_{d(off)}$	Turn-off delay time		-	68	-	
t_{fv}	Fall time		-	25	-	

Switch Position Gate Charge Electrical Characteristics ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Symbols	Parameter	Condition(s)	Values			Units
			Min.	Typical	Max.	
Q_{gs}	Gate to source charge	$V_{DD} = 800\text{ V}, V_{GS} = -4\text{ to }20\text{ V}$ $I_D = 120\text{ A}$	-	143	-	nC
Q_{gd}	Gate to drain charge		-	260	-	
Q_g	Gate charge total		-	545	-	

Diode Position Electrical Characteristics ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Symbols	Parameter	Condition(s)	Values			Units
			Min.	Typical	Max.	
V_{FM}	Forward voltage	$I_F = 60\text{ A}$	-	1.65	-	V
		$I_F = 60\text{ A}, T_J = 200\text{ }^\circ\text{C}$	-	2.5	-	
I_R	Reverse current	$V_R = 1200\text{ V}$	-	TBD	-	μA
		$V_R = 1200\text{ V}, T_J = 200\text{ }^\circ\text{C}$	-	TBD	-	
Q_C	Capacitive charge	$V_R = 1200\text{ V}, I_F = 120\text{ A}, di/dt = 7500\text{ A}/\mu\text{s}$	-	780	-	nC

Thermal Characteristics ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Symbols	Parameter	Condition(s)	Values			Units
			Min.	Typical	Max.	
$R_{\theta(j-c)}$	FET thermal resistance junction-case			0.125		$^\circ\text{C}/\text{W}$

Power Module Mechanical Characteristics

Symbols	Parameter	Condition(s)	Values			Units
			Min.	Typical	Max.	
w	Weight			140		g
M _s	Lead frame mounting torque	6-32 steel screw for lead frame, 10-32 steel screw for baseplate		40		in·lb

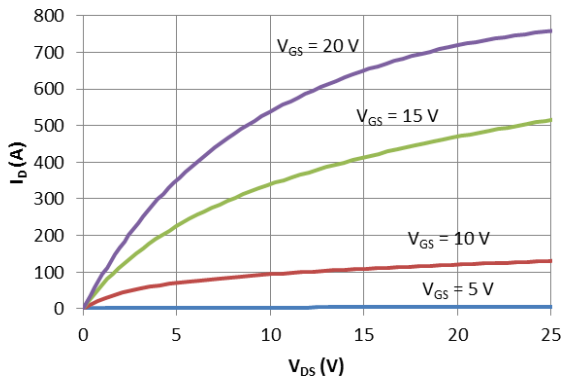
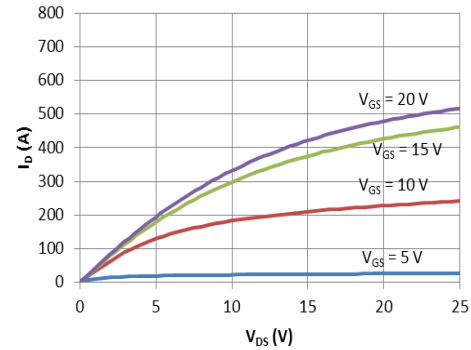
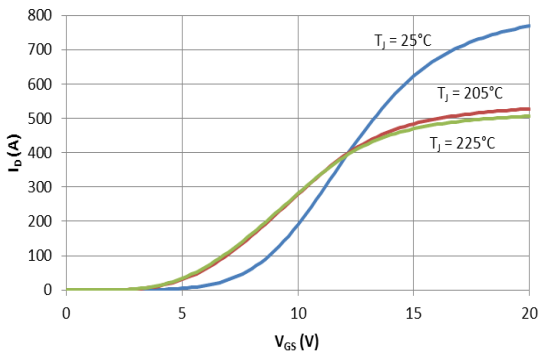
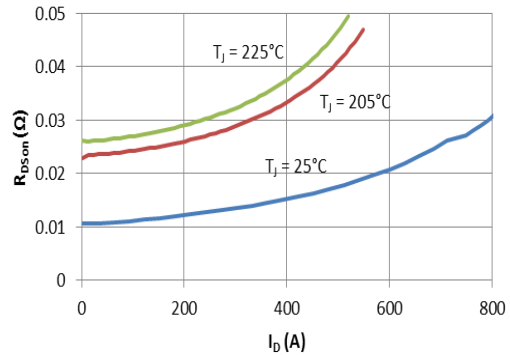
TYPICAL PERFORMANCE CURVES

 Fig. 1 - Typical Output Characteristics, $T_j = 25^\circ\text{C}$

 Fig. 2 - Typical Output Characteristics, $T_j = 205^\circ\text{C}$


Fig. 3 - Transconductance


 Fig. 4 - Typical On Resistance, $V_{GS} = 20\text{ V}$

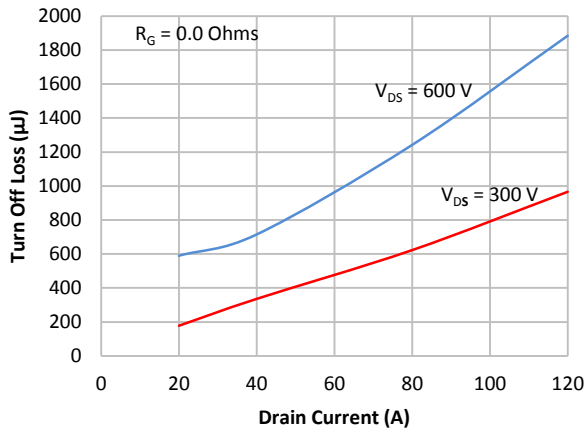


Fig. 5 – Turn off loss versus drain current

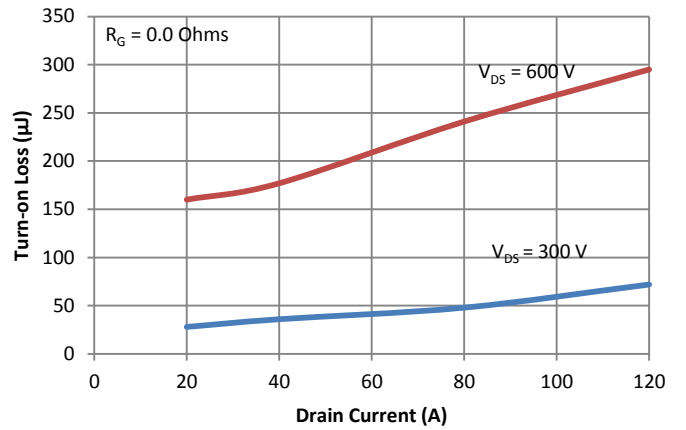


Fig. 6 – Turn on loss versus drain current

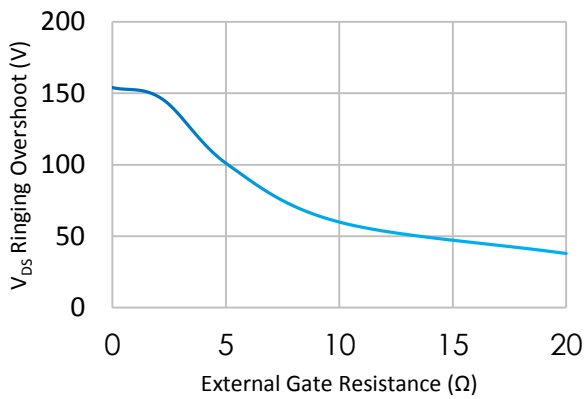


Fig. 7 – Ringing voltage overshoot versus external gate resistance

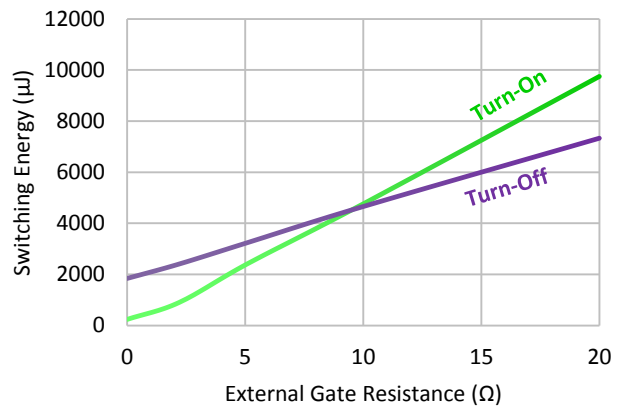


Fig. 8 – Switching energy versus external gate resistance

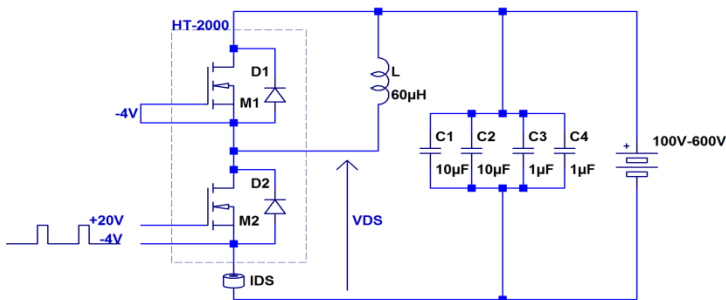
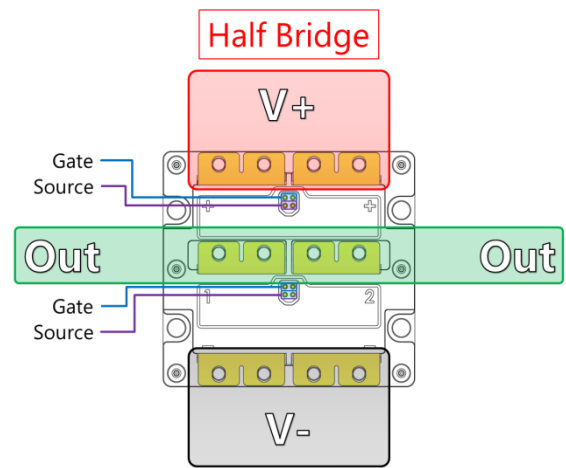


Fig. 9 - Energy values obtained using companion gate driver ($T_{amb} = 25\text{ }^{\circ}\text{C}$).



Half Bridge Connection

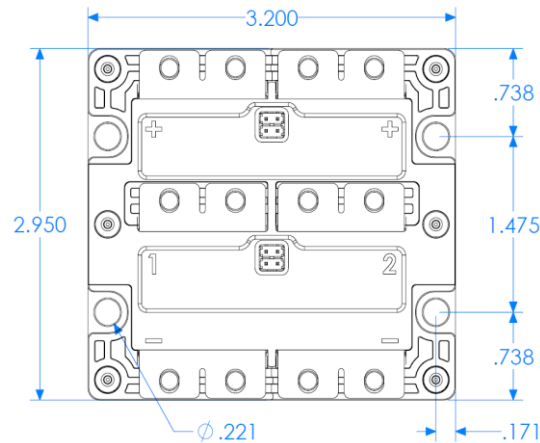
MOUNTING DIMENSIONS

All dimensions are listed in inches

#10-32 bolts are recommended for mounting

A torque of 40 in-lb is recommended

CAD models are available upon request



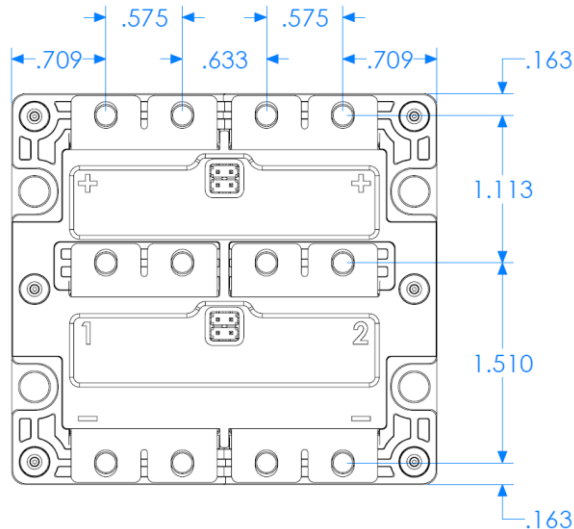
POWER CONTACT DIMENSIONS

All dimensions are listed in inches

#6-32 bolts required for the power contacts

A torque of 40 in-lb is recommended

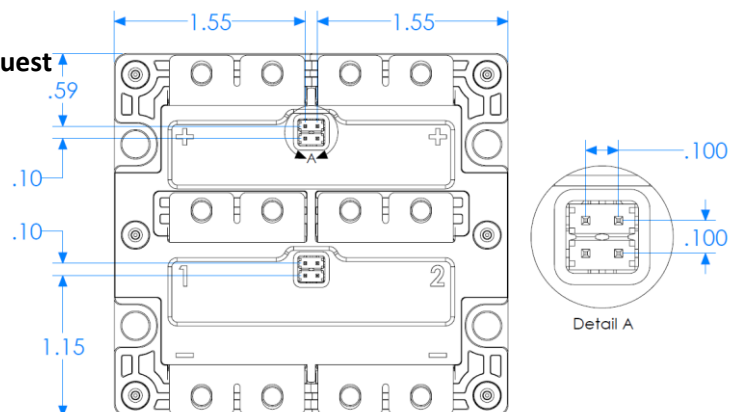
CAD models are available upon request



GATE DRIVE CONNECTIONS

All dimensions are listed in inches

CAD models are available upon request





PRELIMINARY

APE HT-2201

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